(Rev. 8-83)



Form PTO-1449 U.S. Department of Commerce Patent and Trademark Office Attorney Docket No. 0756-1880

Filing Date: November 10, 1998

Serial No. New Application

Applicant: Takashi INUSHIMA et al

Group: 1762

(Use several sheets if necessary)

INFORMATION DISCLOSURE STATEMENT

	(Use several sheets if necessary)		Timing Date: November		G10ap. 1702	800 En
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Serial No. New Application

Applicant: Takashi INUSHIMA et al. 09/188, 382

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U.S. Department of Commerce Patent and Trademark Office

Attorney Docket No. 0756-1880

Serial No. New Application

Applicant: Takashi INUSHIMA et al 09/16, 262

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